

# An IBIS-like Modelling For Power/Ground Noise Induced Jitter Under Simultaneous Switching Outputs (SSO)

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# PRESENTATION OUTLINE

- 1. Introduction**
- 2. Noise and Jitter**
- 3. Analysis of P/G Bouncing under SSO**
- 4. Previous/Related Work**
- 5. IBIS-like Model Derivation and Extraction**
- 6. Model Validation and Jitter Assessment**
- 7. Conclusion**

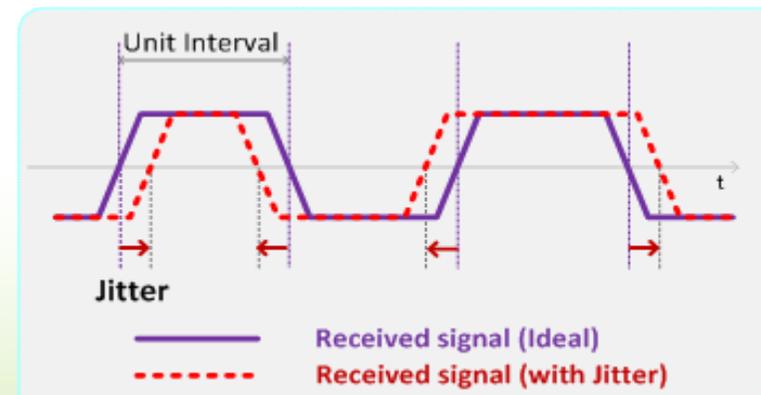
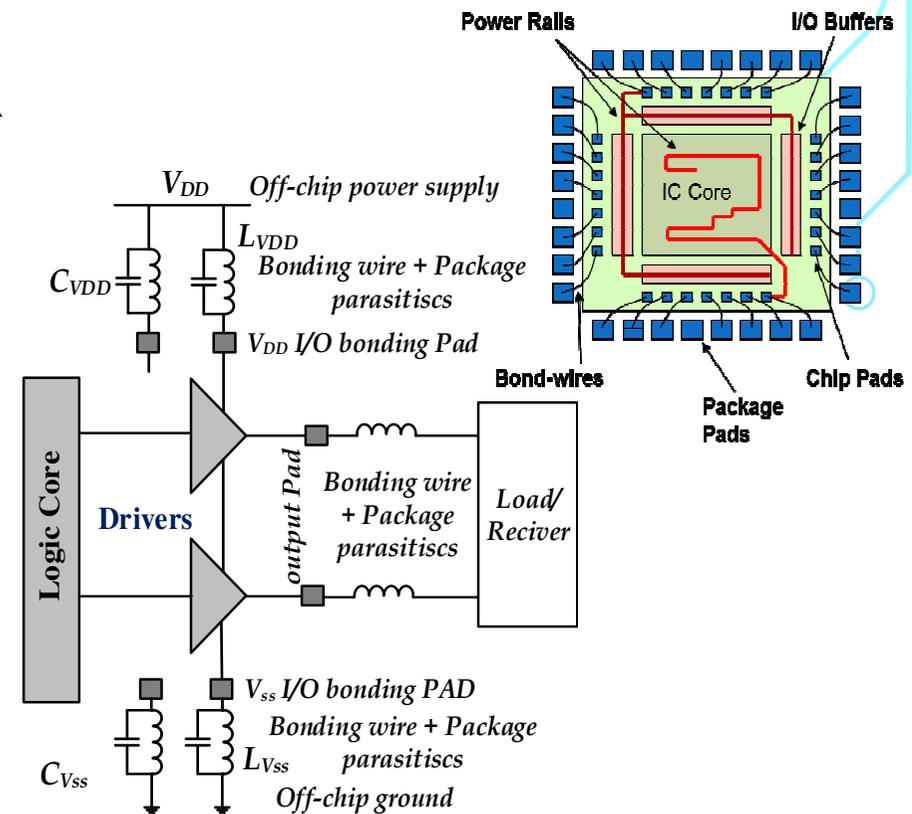
# NOISE AND JITTER

Three main causes of power and ground supply noise:

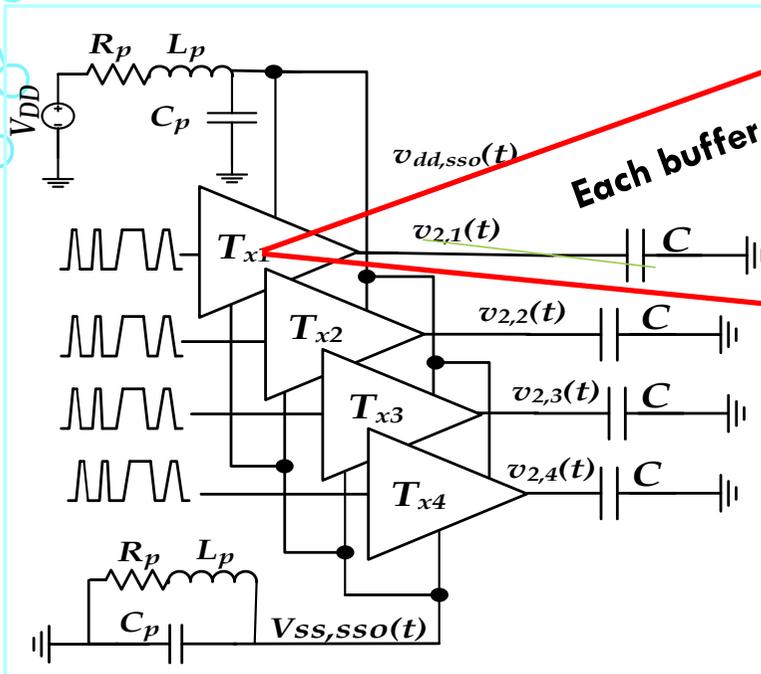
- Power distribution network.
- High speed current  $L di/dt$ .
- Simultaneous switching output buffer.

Jitter is one of the important timing metrics in high-speed systems.

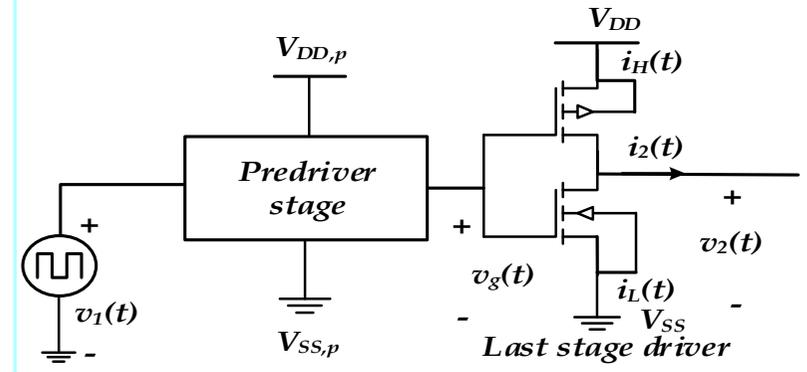
- Is the timing variations in the transition edges from their ideal positions.
- Total jitter (TJ) in a circuit or system can be categorized into two major categories as random jitter (RJ) and deterministic jitter (DJ).



# ANALYSIS OF P/G BOUNCING UNDER SSO: SIMULATION



Each buffer is structured as

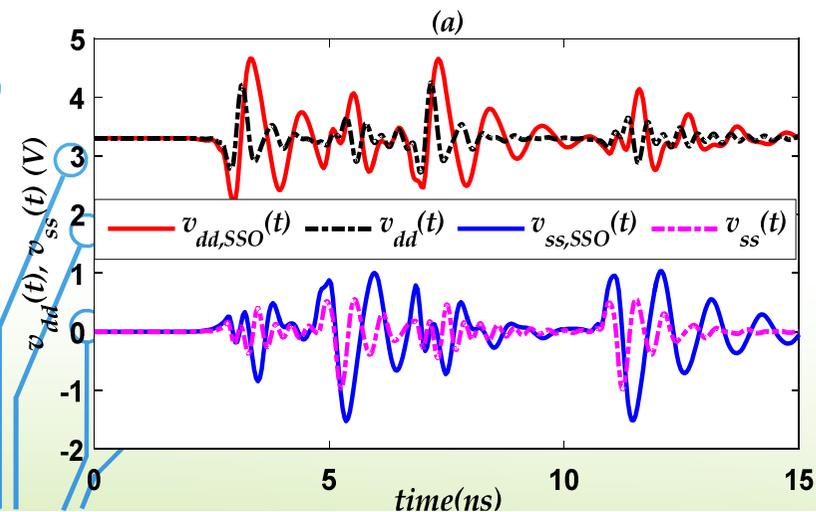
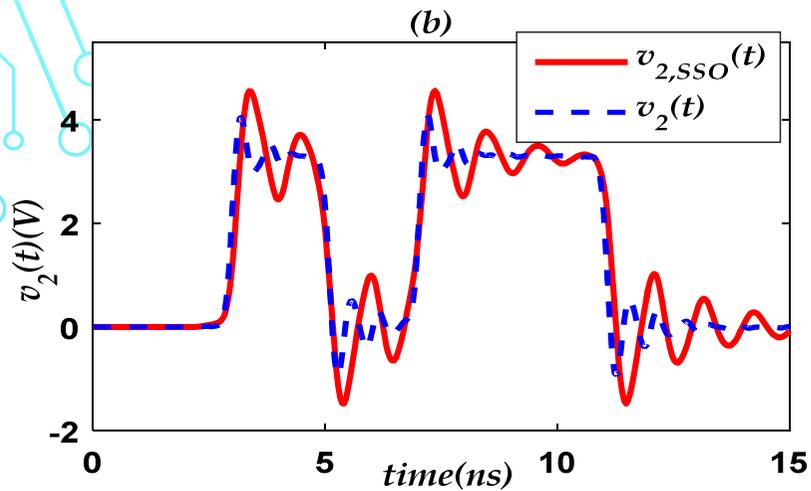


Circuit package parameters:

$$R_p = 20 \text{ m}\Omega, L_p = 2 \text{ nH}, C_p = 2 \text{ pF}, \\ C = 2 \text{ pF}.$$

- The driver is having **four cascaded inverters in series** and designed in  $0.35\mu\text{m}$  technology of TSMC.
- The **first three inverters**: The pre-driver stage. Powered by constant power  $V_{DD,p} = 3.3 \text{ V}, V_{SS,p} = 0 \text{ V}$ .
- These supplies are **isolated** from the ones used for powering the driver's last stage.

# ANALYSIS OF P/G BOUNCING UNDER SSO: RESULTS



- SSO increases the  $di/dt$  noise  $\rightarrow$  Larger variations in  $v_{ss,SSO}(t)$  and  $v_{dd,SSO}(t)$ .

- $\rightarrow$  the output voltage,  $v_2(t)$  overshoot -1.46 V and undershoot 4.56 V.

- $\rightarrow$  High output logic level  $\Delta v_{dd,SSO}/V_{DD}$  is 63.45%

- $\rightarrow$  Low logic level is  $\Delta v_{ss,SSO}/V_{DD}$  73.84%.



SSO noise **Induces both amplitude and jitter (timing) distortions on the output signal.**

# Previous/Related Work

## Previous works :

- Assume the perturbation analysis of the P/G voltage, where linear approximation of the I-V (C-V) functions can be used because the biasing region of the pull-up and pull down transistors of the driver's last stage will not be severely affected.

→ Therefore, **a small signal transistor model** for P/G induced jitter can be used by including the linear capacitive effects.

J. N. Tripathi, P. Arora, H. Shrimali and R. Achar, "Efficient Jitter Analysis for a Chain of CMOS Inverters", IEEE Tran. EMC, pp. 1 – 11, Nov. 2018.

X. Chu, C. Hwang, J. Fan and Y. Li, "Analytic Calculation of Jitter Induced by Power and Ground Noise Based on IBIS I/V Curve", IEEE Tran. EMC, pp. 468 – 477, vol. 60, no. 2, 2018.

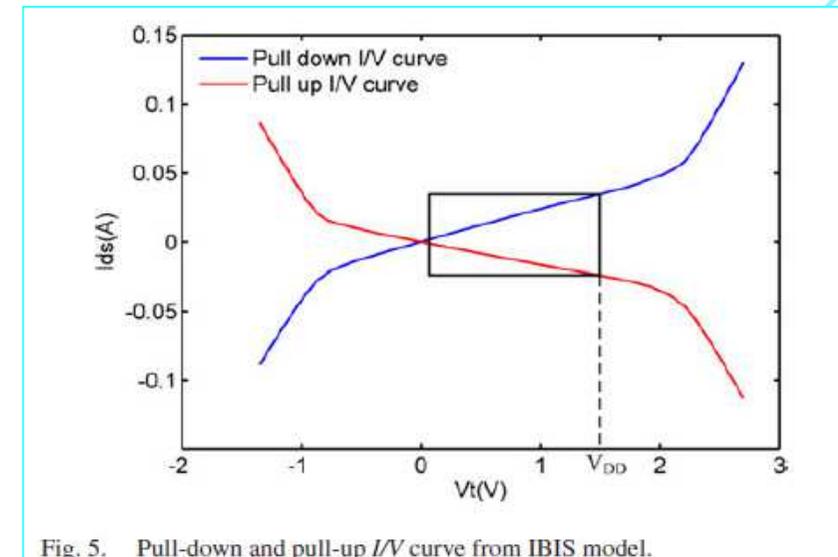


Fig. 5. Pull-down and pull-up I/V curve from IBIS model.

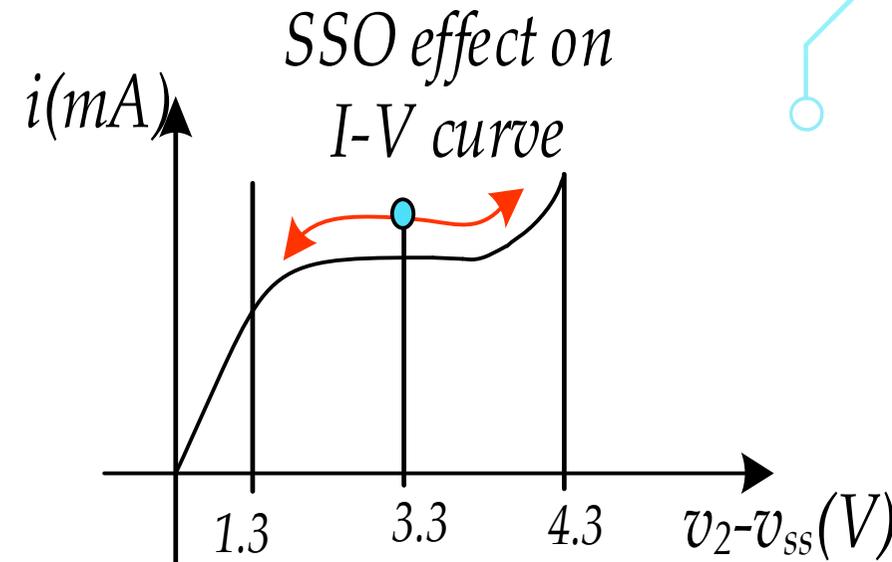
# Problem Statement

The SSO scenario affects the **biasing** and **working regimes** of the **PU** and **PD** transistors forming the last stage of the driver (e.g. linear or saturation).

→ A fully **nonlinear model** for the **driver's last stage** is **required** for accurately **capturing** the P/G induced **jitter** and **distortions**.

→ Considering ONLY the **IBIS I-V curves** that **capture** the **instantaneous static distortions** of the **P/G variation** affects the **prediction accuracy** of **jitter** because of **the overlooked pull-up and pull-down capacitances, ( $C_H$  and  $C_L$ , respectively)**.

X. Chu, C. Hwang, J. Fan and Y. Li, "Analytic Calculation of Jitter Induced by Power and Ground Noise Based on IBIS I/V Curve", IEEE Tran. EMC, pp. 468 – 477, vol. 60, no. 2, 2018.



# Model Derivation and Extraction

# IBIS Model Derivation

- The nonlinear dynamic electrical behaviors of I/O buffer circuit while considering the P/G voltage variables :

$$i_2(t) = w_L(t) F_L \left( x_{dd}(t), \frac{dx_{dd}(t)}{dt} \right) + w_H(t) F_H \left( x_{ss}(t), \frac{dx_{ss}(t)}{dt} \right) \quad (1)$$

Switching Time Signals

$$x_{dd}(t) = v_{dd}(t) - v_2(t) \quad x_{ss}(t) = v_2(t) - v_{ss}(t)$$

Regressor vector applied to the  $F_L(\cdot)$  and  $F_H(\cdot)$  functions

$F_L(\cdot)$  and  $F_H(\cdot)$  model the nonlinear dynamic output admittances of the driver's last stage under low and high input logic levels.

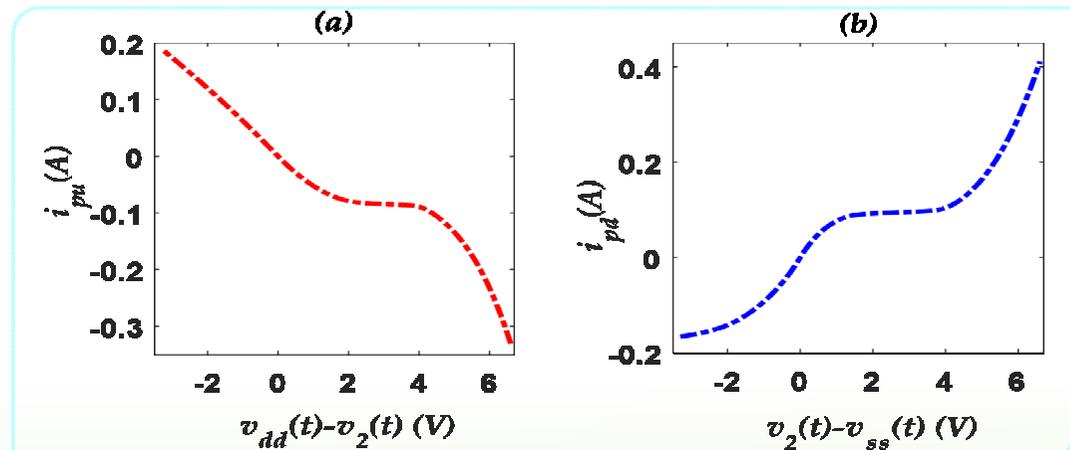
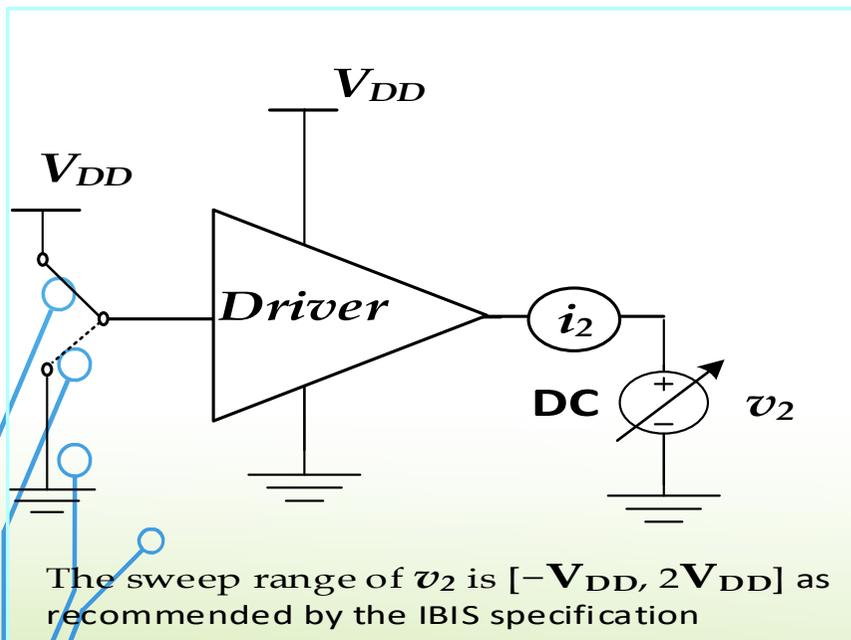
This model takes into account:

- The I-V static contribution of the P/G voltage fluctuation of the last stage.
- The delay introduced by the PU and PD capacitances → represented by the voltage dependent capacitance (C-V).

# Model Extraction : I-V Functions

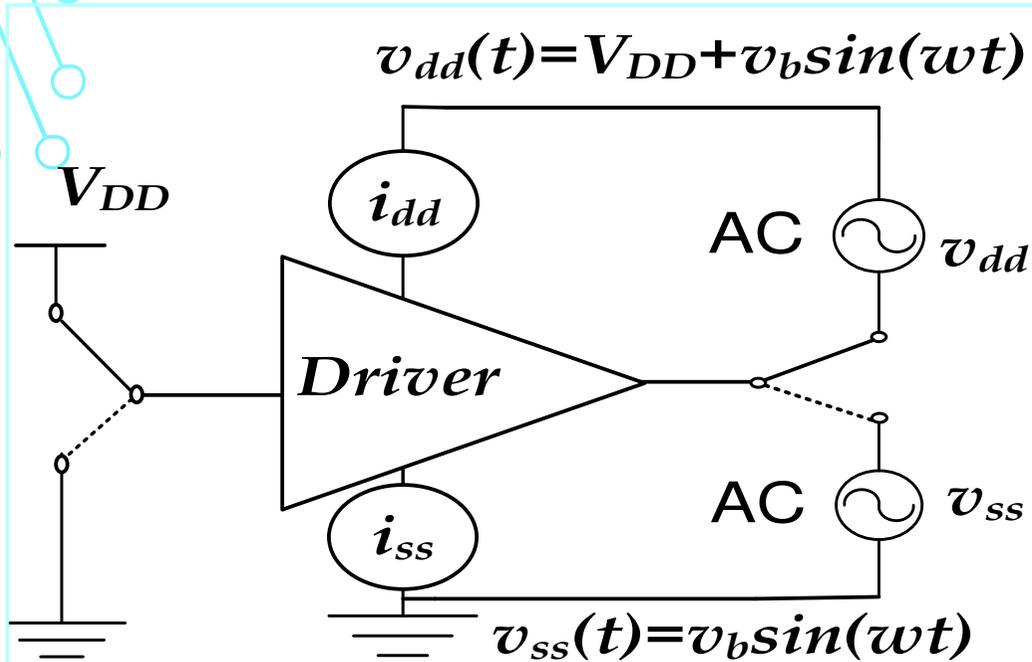
- The nonlinear I-V relationships: 
$$\begin{cases} i_H(t) = I_H(x_{dd}(t)) + C_H \frac{dx_{dd}(t)}{dt} \\ i_L(t) = I_L(x_{ss}(t)) + C_L \frac{dx_{ss}(t)}{dt} \end{cases} \quad (2)$$

$I_H(\cdot)$  and  $I_L(\cdot)$  functions model the nonlinear I-V relationship of the last stage formed by the PU and PD MOSFET transistors and the protection diodes.



Static dc I-V characteristic according to IBIS specifications (a) PU I-V curve, (b) PD I-V curve.

## Model Extraction : C-V Function



$$C_H(v_b) = \text{imag}(Y_{11,H})/\omega$$

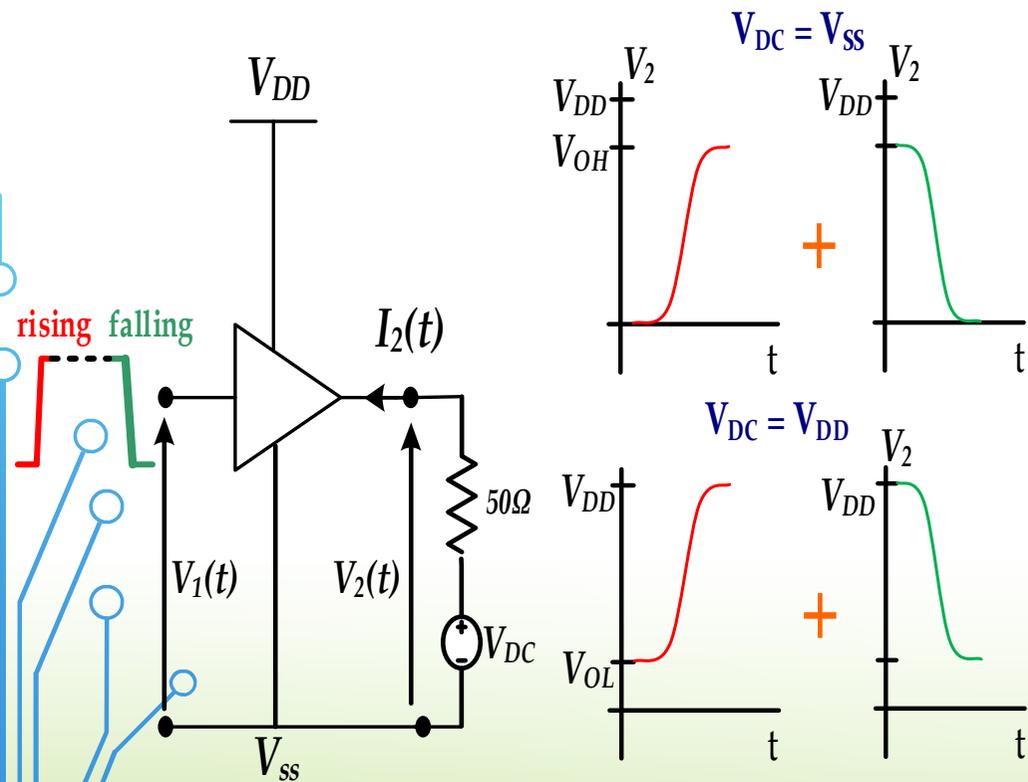
$$C_L(v_b) = \text{imag}(Y_{11,L})/\omega$$

$v_b$  sweep range is  $[-V_{DD}, 2V_{DD}]$

- The  $C_H$  and  $C_L$ , capture the dynamic distortion of the P/G variation on the output signals.
- The capacitive effects improves the accuracy of the jitter prediction induced by the P/G voltage variations.

# Model Extraction : switching timing signals $w_L(t)$ and $w_H(t)$

## Setup for switching timing signals extraction

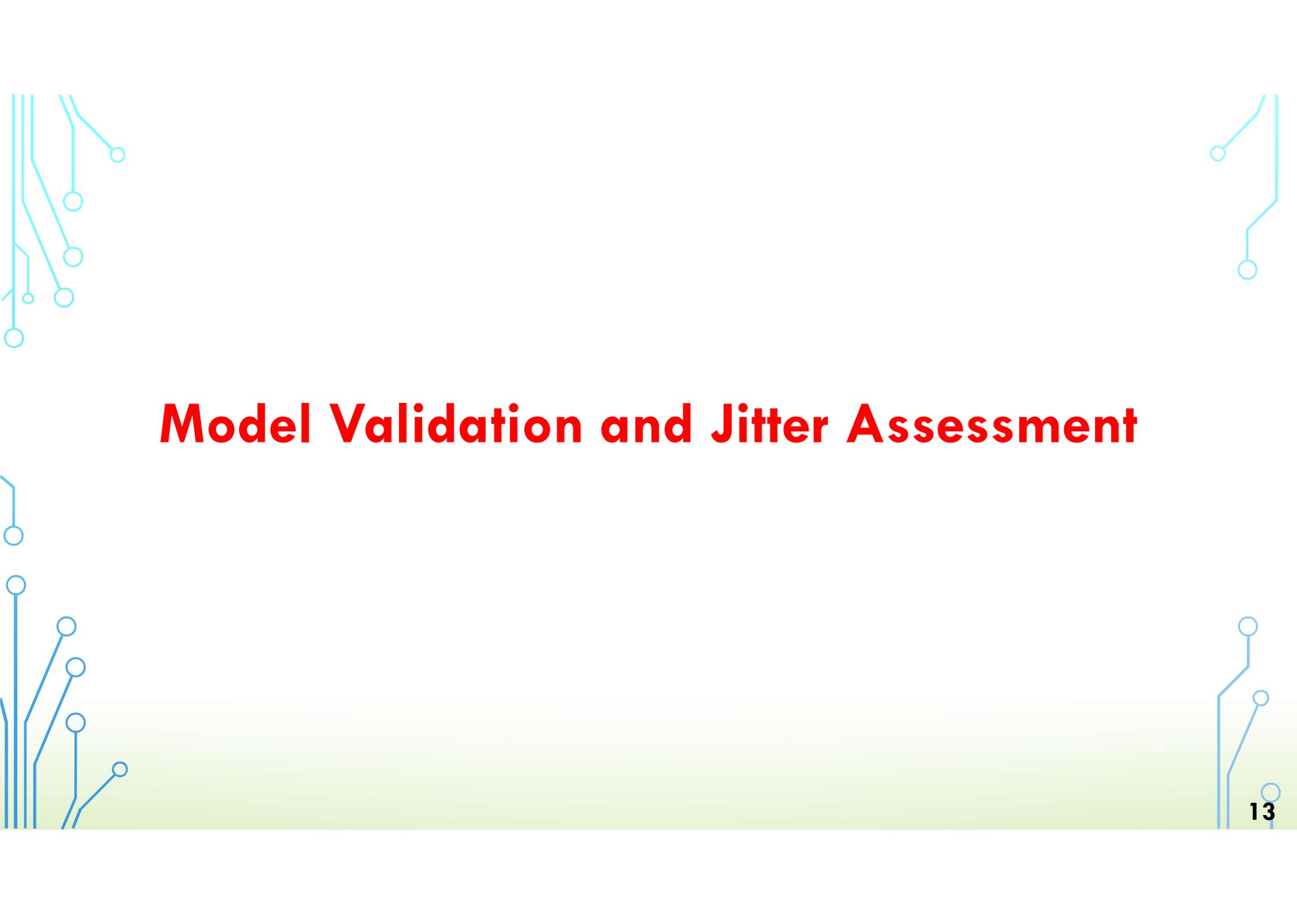


## The $w_L(t)$ and $w_H(t)$ functions :

- ✓ capture the predriver's input-output timing distortions extracted by means of the two equations with two unknowns (2E2U) algorithm

$$\begin{bmatrix} w_L^n(t) \\ w_H^n(t) \end{bmatrix} = \begin{bmatrix} I_{L,b}^n(t) & I_{H,b}^n(t) \\ I_{L,a}^n(t) & I_{H,a}^n(t) \end{bmatrix}^{-1} \cdot \begin{bmatrix} I_{2,a}^n(t) \\ I_{2,b}^n(t) \end{bmatrix}$$

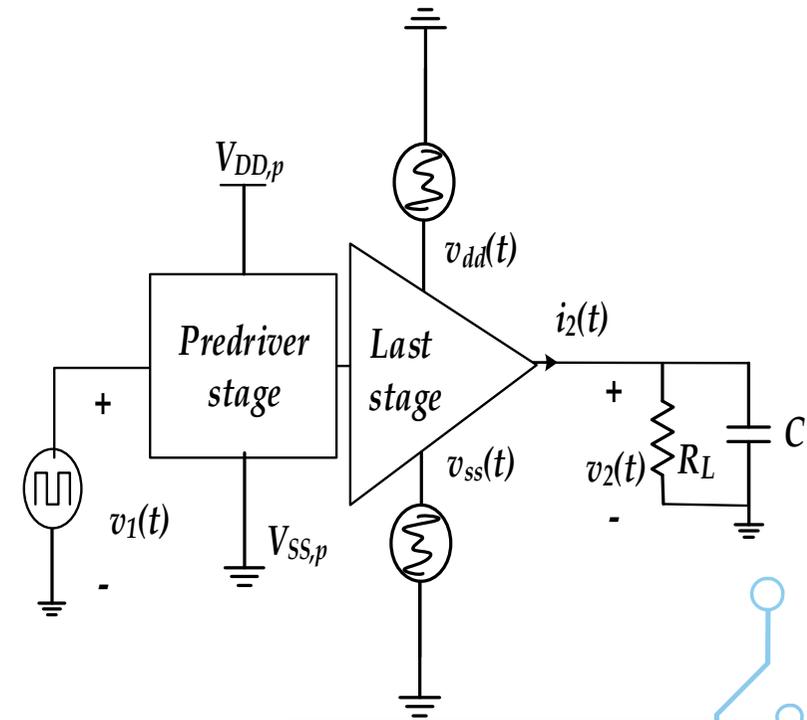
- ✓ The  $w_L(t)$  and  $w_H(t)$  functions are assumed to be mildly affected by the P/G bouncing effect



# Model Validation and Jitter Assessment

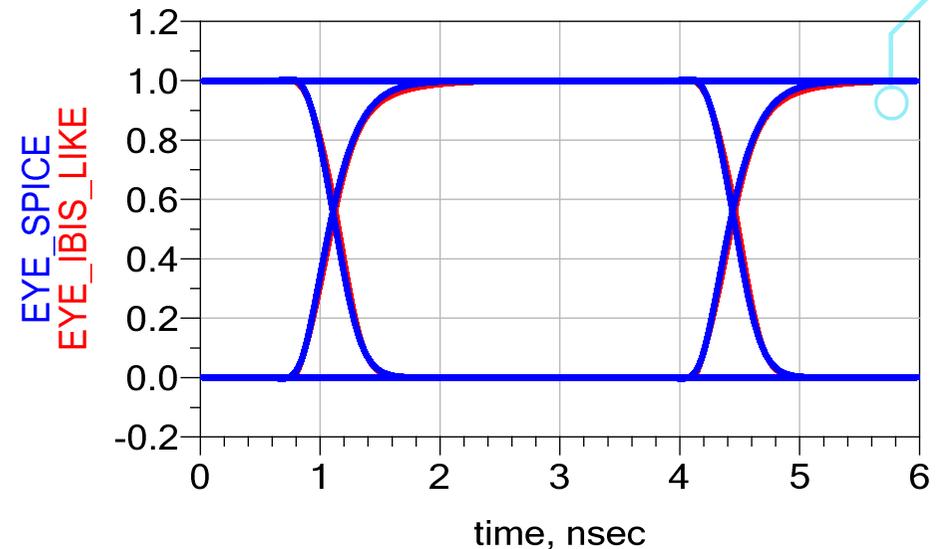
# Model Validation and Implementation

- The I-V and C-V functions were implemented as look-up tables in MATLAB Simulink time domain solver.
- The pull up and pull down capacitances are connected between the power-output-pin and the ground-output-pin.
- The  $w_L(t)$  and  $w_H(t)$  functions are computed offline and implemented as piece-wise linear signal using the repeating sequence block.
- Three test cases was performed for predicting jitter under constant and P/G voltage variations.



## Test case 1: Eye Diagram prediction under constant P/G voltage

- The developed model is able to accurately predict the inherent drive's jitter distortions under constant P/G supply voltages.
  - ✓ **The prediction error of eye's jitter and width are 0.34% and 0.15%.**
- These measurements were carried out under:
  - ✓ 40-60% eye boundary, which indicates the measurement region between eye crossing points
  - ✓ the eye threshold levels are the 20% to 80% points on the rising and falling transitions.



**Jitter performance: IBIS-like vs. Spice-level models**

Model	Spice-based	IBIS-like
Performance		
Eye jitter (pp) (ps)	59.56	59.30
Eye width (ns)	3.33	3.335
Eye height (V)	3.29	3.284

## Test case 2: Timing signal prediction under two-tone P/G signals

- $v_{dd}(t)$  and  $v_{ss}(t)$  are represented by:

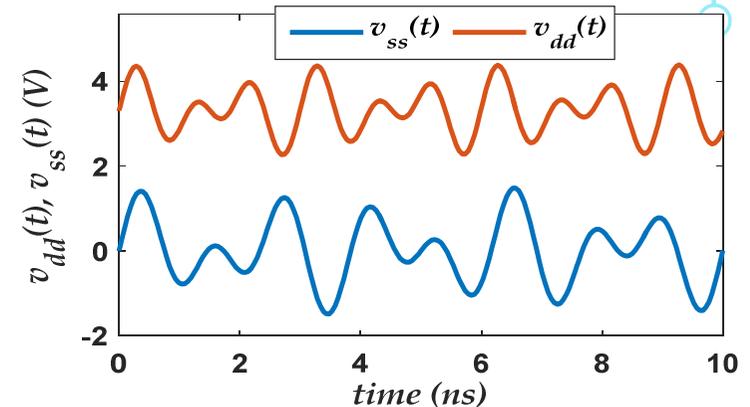
$$\begin{cases} v_{dd}(t) = V_{DD} + a_1 \sin(2\pi f_1 t) + a_2 \sin(2\pi f_2 t) \\ v_{ss}(t) = a_3 \sin(2\pi f_3 t) + a_4 \sin(2\pi f_4 t) \end{cases}$$

where  $f_1 = 1 \text{ GHz}$ ,  $a_1 = 0.6 \text{ V}$ ,  $a_2 = 0.5 \text{ V}$ ,  $f_2 = 670 \text{ MHz}$ ,  $f_3 = 550 \text{ MHz}$ ,  $a_3 = 0.5 \text{ V}$ ,  $a_4 = 0.8 \text{ V}$  and  $f_4 = 800 \text{ MHz}$ .

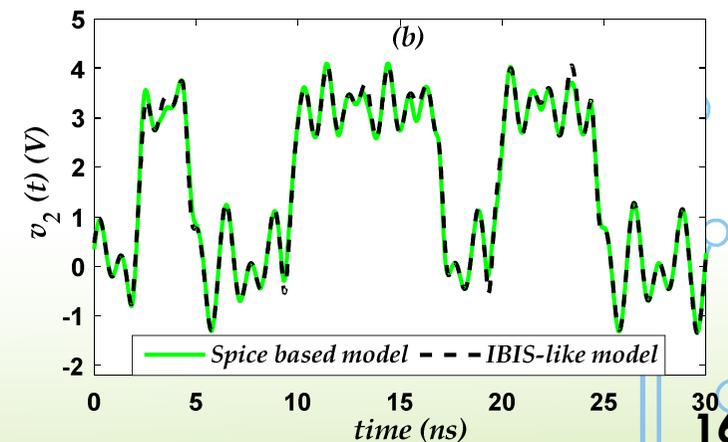
- This P/G validation signals ensure almost **66.66%** peak-to-peak (pp) of the P/G voltage variations around the nominal voltage supply  $V_{DD}$ .

→ The error was less than **0.47 V** which represents less than **8%** of the of  $v_{2,pp}(t)$  (e.g. peak-to-peak).

P/G voltage waveforms used in test case # 2



Prediction of the  $v_2(t)$  waveform.



## Test case 3: Eye diagram prediction under sinusoidal P/G variations

The model is validated by superimposing 4 sinusoidal signals at the P/G terminals.

$$\begin{cases} v_{dd}(t) = V_{DD} + \sum_{i=1}^4 a_i \sin(2\pi f_{di}t) \\ v_{ss}(t) = \sum_{i=1}^4 b_i \sin(2\pi f_{si}t) \end{cases}$$

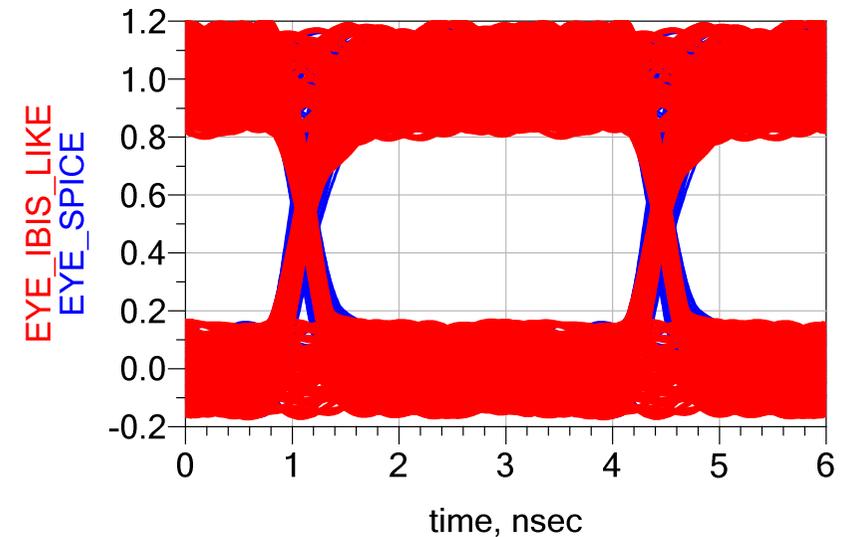
• The amplitude and frequency parameters:

$$a_i = \{0.4, 0.05, 0.2, 0.1\} V; f_{di} = \{328, 100, 625, 833\} MHz,$$

$$b_i = \{0.2, 0.3, 0.1, 0.1\} V; f_{si} = \{250, 370, 870, 628\} MHz.$$

The prediction accuracy of IBIS-like model :

- eye's jitter is 7.06 %
- Eye width is 2.59%



Jitter performance: IBIS-like vs. Spice-level models

Model	Spice-based	IBIS-like
<b>Performance</b>		
Eye jitter (pp) (ps)	257.30	240.33
Eye width (ns)	3.08	3.16
Eye height (V)	2.21	2.13

# CONCLUSION

- This work has evaluated the performance of the proposed IBIS-like model formulation and extraction for predicting the P/G voltage variations in different validation scenarios that emulate the SSO case where the fast bouncing P/G voltage supplies are large in magnitude.
  - A nonlinear I-V and C-V model for the PU and PD devices are required to capture the static effects of the variation of the supply voltages.
  - The simple linear capacitive model should be extended to a nonlinear case while the model should be validated with higher clock rates to assess its jitter predicting capabilities.
  - A generic I/O buffer circuit structure should be considered where the pre-driver's and last stage are powered by the same voltage supplies.